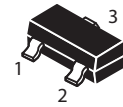
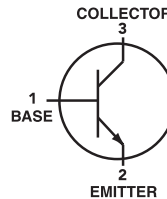


**NPN General Purpose Transistors**
 **Lead(Pb)-Free**

**SOT-23**
**MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	$V_{CEO}$	25	Vdc
Collector-Base Voltage	$V_{CB0}$	40	Vdc
Emitter-Base Voltage	$V_{EBO}$	5.0	Vdc
Collector Current-Continuous	$I_C$	500	mAdc

**THERMAL CHARACTERISTICS**

Characteristics	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (1) $T_A=25^{\circ}\text{C}$ Derate above $25^{\circ}\text{C}$	$P_D$	225	mW
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	1.8	$\text{mW}/^{\circ}\text{C}$
Total Device Dissipation Alumina Substrate, (2) $T_A=25^{\circ}\text{C}$ Derate above $25^{\circ}\text{C}$	$P_D$	300	mW
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	2.4	$\text{mW}/^{\circ}\text{C}$
Junction and Storage, Temperature	$T_J, T_{stg}$	-55 to +150	$^{\circ}\text{C}$

**DEVICE MARKING**
**S9013LT1=J3**
**ELECTRICAL CHARACTERISTICS**

Characteristics	Symbol	Min	Max	Unit
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**OFF CHARACTERISTICS**

Collector-Emitter Breakdown Voltage ( $I_C=0.1\text{mAdc}, I_B=0$ )	$V_{(BR)CEO}$	25	-	Vdc
Collector-Base Breakdown Voltage ( $I_C=100\mu\text{Adc}, I_E=0$ )	$V_{(BR)CBO}$	40	-	Vdc
Emitter-Base Breakdown Voltage ( $I_E=100\mu\text{Adc}, I_C=0$ )	$V_{(BR)EBO}$	5.0	-	Vdc
Collector Cutoff Current ( $V_{CE}=20\text{Vdc}, I_E=0$ )	$I_{CEO}$	-	0.1	$\mu\text{Adc}$
Collector Cutoff Current ( $V_{CB}=40\text{Vdc}, I_E=0$ )	$I_{CBO}$	-	0.1	$\mu\text{Adc}$
Emitter Cutoff Current ( $V_{EB}=5.0\text{Vdc}, I_C=0$ )	$I_{EBO}$	-	0.1	$\mu\text{Adc}$

1.FR-5=1.0 x 0.75 x 0.062 in

2.Alumina=0.4 x 0.3 x 0.024 in. 99.5% alumina

**ELECTRICAL CHARACTERISTICS** ( $T_A=25^\circ\text{C}$  unless otherwise noted) (Continued)

Characteristics	Symbol	Min	Max	Unit
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**ON CHARACTERISTICS**

DC Current Gain ( $I_C=50\text{ mAdc}, V_{CE}=1.0\text{ Vdc}$ ) ( $I_C=500\text{ mAdc}, V_{CE}=1.0\text{ Vdc}$ )	$h_{FE}^{(1)}$	120	350	-
	$h_{FE}^{(2)}$	40	-	-
Collector-Emitter Saturation Voltage ( $I_C=500\text{ mAdc}, I_B=50\text{ mAdc}$ )	$V_{CE(sat)}$	-	0.6	Vdc
Base-Emitter Saturation Voltage ( $I_C=500\text{ mAdc}, I_B=50\text{ mAdc}$ )	$V_{BE(sat)}$	-	1.2	Vdc

**SMALL-SIGNAL CHARACTERISTICS**

Current-Gain-Bandwidth Product ( $I_C=20\text{ mAdc}, V_{CE}=6.0\text{ Vdc}, f=30\text{ MHz}$ )	$f_T$	150	-	MHz
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**CLASSIFICATION OF  $h_{FE}$** 

Rank	L	H
Range	120-200	200-350

